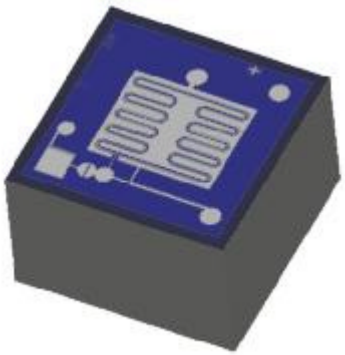
LOW NOISE JFETS

MX16



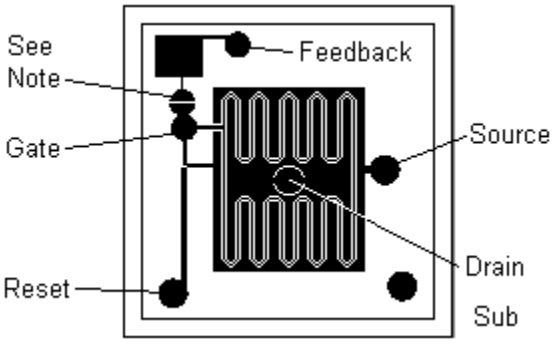
FEATURES

- **Ultra Low Noise**
  - **Less than 1.5nV @ 1KHz, 20ºC**
- **Free of Generation Recombination Noise**
- **Excellent gm to C_{gs} Ratio**
  - **g_m=28mS, C_{gs}=4pF, 20ºC**
- **4-Terminal**
- **N-Channel**
- **Available in Die and Other Packages**

Noise Characteristics Units in nV/√Hz	**Typ**	**Max**	**Test Condition**	**Temp**
1KHz	1.1		V_{ds}=4V, I_d=5mA	20ºC
10KHz	0.8		V_{ds}=4V, I_d=5mA	20ºC
100KHz	0.8		V_{ds}=4V, I_d=5mA	20ºC
1KHz	0.9	1.3	V_{ds}=4V, I_d=5mA	-100ºC
10KHz	0.6	1.0	V_{ds}=4V, I_d=5mA	-100ºC
100KHz	0.6	1.0	V_{ds}=4V, I_d=5mA	-100ºC

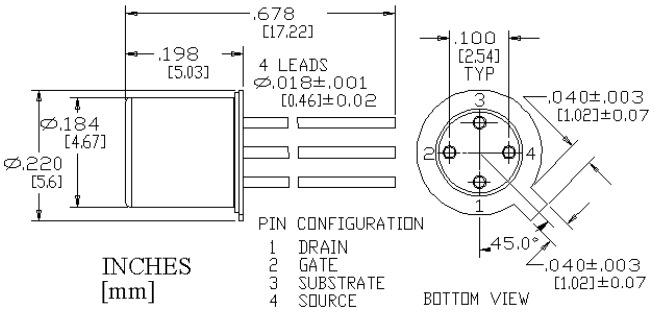
Die Size 0.80mm x 0.80mm x 0.50mm

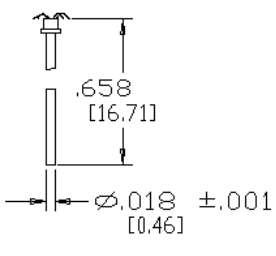
Static Characteristics		**Min**	**Typ**	**Max**	**Unit**	**Test Condition**
Gate to Source Breakdown	BV_{gss}	20	26		V	V_{ds}=0V, I_g=1µA, V_{sub}=0V
Reverse Leakage Current	I_{sub} I_{gss}		0.4		pA	$V_{reverse}$ = -10V
Gate to Source Cutoff Voltage	V_{gs}		10		V	V_{sub}=0V,I_d=1nA
Drain Saturation Current	I_{dss}		300		mA	V_{sub}=0V,V_{gs}=0V
Dynamic Characteristics						
Transconductance	g_m		28 40		mS	V_{ds}=4V, I_d=5mA, 20ºC V_{ds}=4V, I_d=5mA, -100ºC
Gate to Source Capacitance	C_{gs}		4		pF	V_{gs} =0V,V_{ds}=4V, I_d=5mA

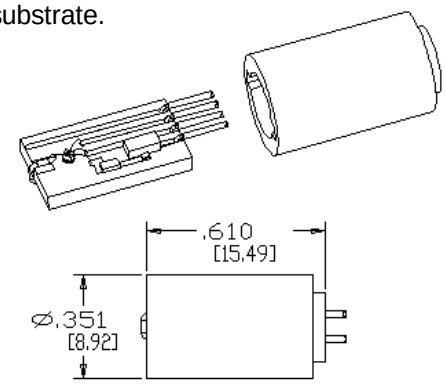


The bottom gate on this 4 terminal JFET is the substrate.

AVAILABLE JFET PACKAGE:







TO-72 PACKAGE NAILHEAD FLYING LEADS TEFLON PACKAGE